#### SILICON (Si) POWER MOSFET A CEZ10R10A

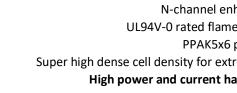


# **CEZ10R10A**

# 100V A 8mΩ A 64A A Si MOSFET

SILICON SI MOSFET A SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy PPAK5x6 package ▲ MSL 3 Super high dense cell density for extremely low R<sub>DS(ON)</sub> High power and current handling capability

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**MAXIMUM RATINGS** 

Parameter (T <sub>A</sub> = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	100V
Gate-Source Voltage	V <sub>GS</sub>	±20V
Continuous Drain Current at R <sub>TH_JC</sub>	I <sub>D</sub>	64A
Continuous Drain Current at R <sub>TH_JA</sub>	I <sub>D</sub>	19A
Pulsed Drain Current Note 1	I <sub>DM</sub>	256A
Pulsed Drain Current Note 1	I <sub>DM</sub>	76A
Maximum Power Dissipation	PD	71W
Single Pulsed Avalanche Energy Note 5	E <sub>AS</sub>	56mJ
Single Pulsed Avalanche Current Note 5	I <sub>AS</sub>	15A
Operating and Storage Temperature Range	Т <sub>J</sub> , Т <sub>STG</sub>	-55°C to +150°C

RoHS

REACH

HALOGEN

FREE

#### **THERMAL CHARACTERISTICS**

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R <sub>TH_JC</sub>	1.75°C/W
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH_JA</sub>	20°C/W

#### **APPLICATIONS**

Battery Management Systems	E-Bike	Industrial Control	Power Inverter	UPS
+ 4 -	50			

#### **PIN DESCRIPTION**

Circuit Diagram	Outline - Bottom View	Pin No.	Description
G (4) S (1,2,3)		1 2 3 4 5	Source Source Gate Drain

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# **ELECTRICAL CHARACTERISTICS A T**<sub>A</sub> = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV <sub>DSS</sub>	100			V
Zero Gate Voltage Drain Current	$V_{DS} = 80V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -20V, $V_{DS}$ = 0V	I <sub>GSSR</sub>			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 20A$	R <sub>DS(ON)</sub>		8	9.6	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 6V, I_{D} = 10A$	R <sub>DS(ON)</sub>		12	15.5	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	C <sub>ISS</sub>		1395		рF
Output Capacitance	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$	Coss		541		рF
Reverse Transfer Capacitance	$V_{DS}$ = 50V, $V_{GS}$ = 0V, f = 1MHz	C <sub>RSS</sub>		5		рF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{\text{G}(\text{ext})}$ = 6 $\Omega$	t <sub>D(ON)</sub>		29		ns
Turn-On Rise Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(ext)}$ = $6\Omega$	t <sub>R</sub>		7		ns
Turn-Off Delay Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{\text{G}(\text{ext})}$ = 6 $\Omega$	t <sub>D(OFF)</sub>		48		ns
Turn-Off Fall Time	$V_{\text{DD}}$ = 30V, $V_{\text{GS}}$ = 10V, $I_{\text{D}}$ = 1A, $R_{G(ext)}$ = $6\Omega$	t <sub>F</sub>		23		ns
Total Gate Charge	$V_{DS} = 50V, V_{GS} = 6V, I_D = 10A$	$Q_{G}$		19		nC
Gate Source Charge	$V_{DS} = 50V, V_{GS} = 6V, I_D = 10A$	Q <sub>GS</sub>		6		nC
Gate Drain Charge	$V_{DS}$ = 50V, $V_{GS}$ = 6V, $I_{D}$ = 10A	$\mathbf{Q}_{GD}$		11		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current <sup>Note3</sup>		١ <sub>s</sub>			64	A
Drain-Source Diode Forward Voltage <sup>Note3</sup>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A	$V_{\text{SD}}$			1.1	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board,  $t \le 10$  sec

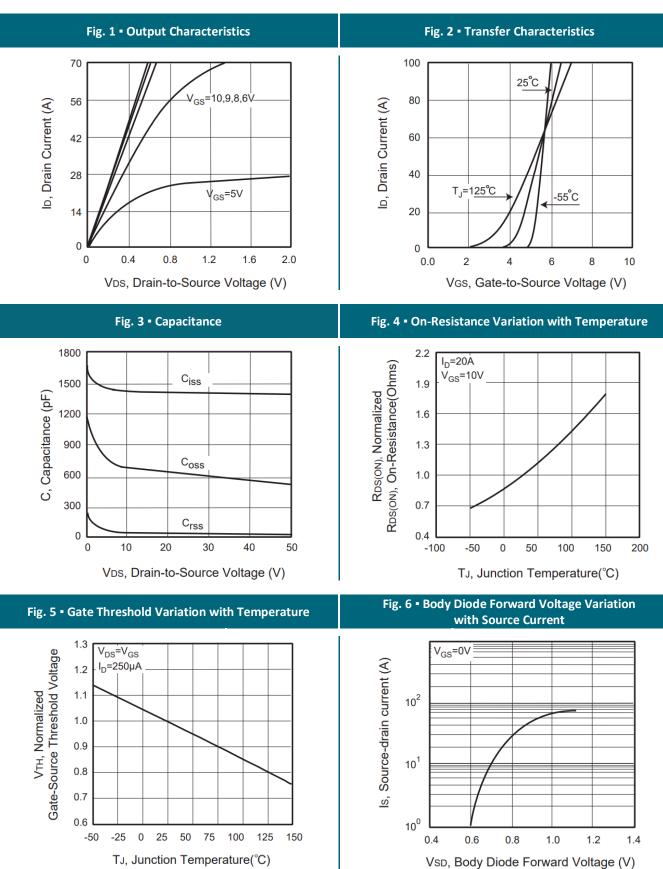
3: Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4: Guaranteed by design, not subject to production testing.

5: L = 0.5mH,  $I_{AS} = 15A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^{\circ}C$ 

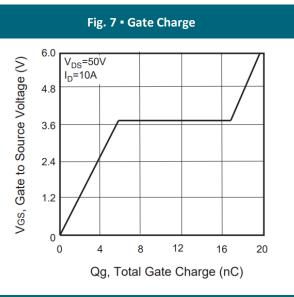


### **REFERENCE DATA A TYPICAL DEVICE PERFORMANCE**





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#### Fig. 9 - Breakdown Voltage Variation vs. Temperature

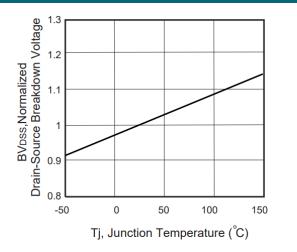
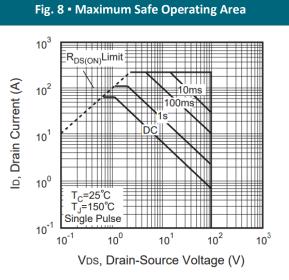
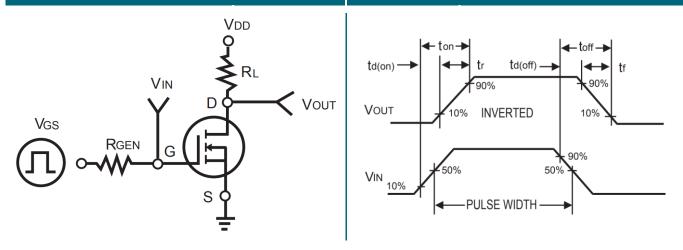


Fig. 10 - Switching Test Circuit





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# **REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE**

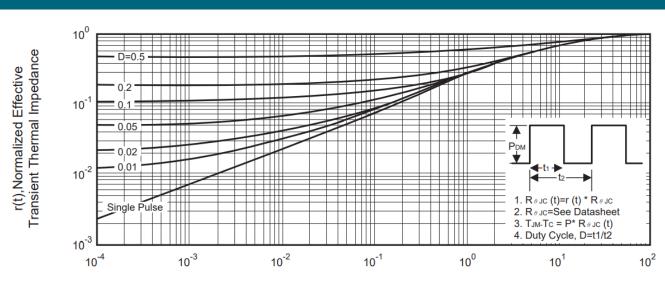
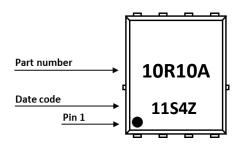


Fig. 12 • Normalized Thermal Transient Impedance Curve

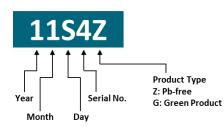
Square Wave Pulse Duration (sec)

#### PART MARKING



#### DATE CODE

#### Example: 11S4Z



Coding list for "Day"										
1	2	3	4	5	6	7	8	9	Α	
01	02	03	04	05	06	07	08	09	10	
В	С	D	Ε	F	G	Н	I	J	K	
11	12	13	14	15	16	17	18	19	20	
L	Μ	Ν	0	Ρ	Q	R	S	Т	U	
21	22	23	24	25	26	27	28	29	30	
v										
31										

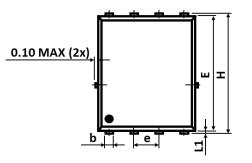
Coding list for "Month"

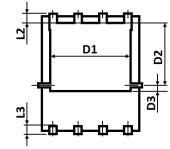


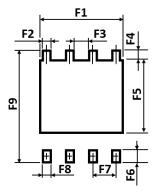
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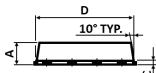


# PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT









Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	0.800	-	1.170	E	5.650	-	5.900
b	0.340	-	0.490	е		1.270 TYP	
С	0.200	-	0.340	Н	5.900	-	6.150
D	4.800	-	5.100	L1	0.050	-	0.250
D1	3.800	-	4.200	L2	0.380	-	0.620
D2	3.180	-	3.780	L3	0.380	-	0.750
D3	0.150	-	0.360				

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	4.500	-	F6	-	0.800	-
F2	-	0.500	-	F7	-	1.270	-
F3	-	0.770	-	F8	-	0.500	-
F4	-	0.550	-	F9	-	6.250	-
F5	-	3.650	-				

Notes: 1. The suggested land pattern dimensions have been provided for reference only. 2. For further information, please reference document IPC-7351A.

#### **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CEZ10R10A	PPAK 5x6	Reel	2,500pcs	5,000pcs	40,000pcs	

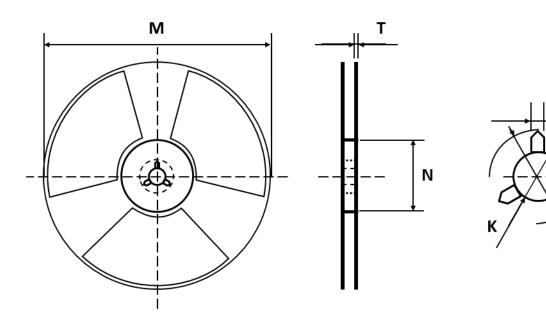


S

Н

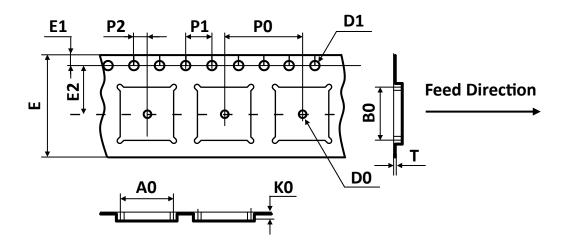


#### **REEL DIMENSIONS** All dimensions in mm



Tape Size	Reel Size	М	N	т	Н	К	S
		Ø330.00	Ø100.00	2.10	22.00	13.00	2.00
12mm	Ø330	±2.00	±1.00	±0.20	±0.50	+0.50 -0.20	±0.50

# TAPE DIMENSIONS All dimensions in mm



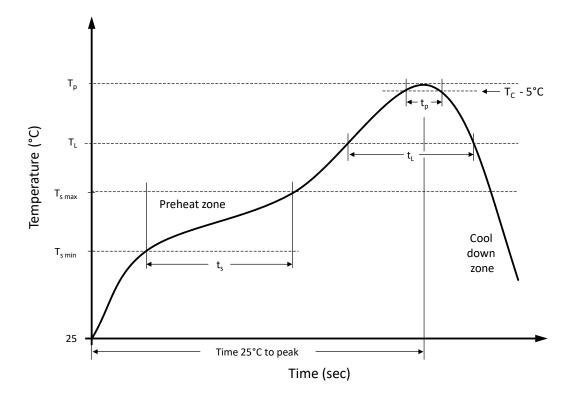
Package	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	т
	6.50	5.28	2.00	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
PPAK 5x6	±0.10	±0.10	±0.10	±0.25	±0.10	+0.30 -0.10	±0.10	±0.05	±0.10	±0.10	±0.05	±0.02







#### **RECOMMENDED REFLOW SOLDERING PROFILE**



#### **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{smin}$	100 °C	150 °C
Preheat temperature max.	$T_{s max}$	150 °C	200 °C
Preheat time $t_s$ from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T <sub>L</sub> to T <sub>p</sub> )		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	TL	183 °C	217 °C
Time $t_L$ maintained above $T_L$	t∟	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate ( $T_L$ to $T_p$ )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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